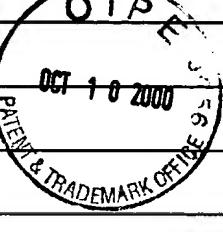


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				APPLICANT(S) TANABE et al			
				FILING DATE 7/7/2000	GROUP 1700		
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
							
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
		7-118443	12/18/95	JAPAN	H01L	21/20	YES <input checked="" type="checkbox"/> NO <input type="checkbox"/>
GSE		5-211167	8/20/93	JAPAN	H01L	21/336	<input checked="" type="checkbox"/>
GSE		5-909191	4/9/93	JAPAN	H01L	21/268	<input checked="" type="checkbox"/>
GSE		5-182923	7/23/93	JAPAN	H01L	21/268	<input checked="" type="checkbox"/>
GSE		7-99321	4/11/95	JAPAN	H01L	29/186	<input checked="" type="checkbox"/>
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
GSE			Crystalline Si Films for Integrated Active-Matrix Liquid-Crstal Displays, James S. Im and Robert S. Sposili, Mrs Bulletin, March 1996, pages 39-48.				
GSE			Sequential Lateral Solidification of Thin Silicon Films on SiO ₂ , Robert S. Sposili and James S. Im, Appl. Phys. Lett. 69 (19), 4 November 1996, pages 2864-2866				
EXAMINER				DATE CONSIDERED			
<i>Geoffrey L Evans</i>				<i>November 18, 2001</i>			

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				FILING DATE 7/7/2000	GROUP 1706		
U.S. PATENT DOCUMENTS							
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FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
GSE	9-7911	1/10/97	JAPAN	HO1L	21/02	✓	
GSE	9-17729	1/17/97	JAPAN	HO1L	21/20	✓	
GSE	9-148246	6/6/97	JAPAN	HO1L	21/20	✓	
GSE	10-116989	5/6/98	JAPAN	HO1L	29/786	✓	
GSE	10-149984	6/2/98	JAPAN	HO1L	21/20	✓	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
GSE		Single-crystal Si Films for Thin-Film transistor Devices, James S. Im, Robert S. Sposili, and M.A. Crowder, Appl. Phys. Lett. 70 (25), 23 June 1997, American Institute of Physics, page 3434-3436.					
GSE		Effects of Light Pulse Duration on Excimer-Laser Crystallization Characteristics of Silicon Thin Films, Ishihara, Yeh, Hattori and Matsumura, Jpn. J. Appl. Phys. Vol. 34 (1995) pp. 1759-1764, Page 1, No. 4A, April 1995.					
EXAMINER <i>Geoffrey L. Evans</i>				DATE CONSIDERED <i>November 18, 2000</i>			

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O I P E OCT 10 2000 JC56 PATENT & TRADEMARK OFFICE						
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS
TRANSLATION YES NO						
6SE		11-17185	1/22/99	JAPAN	HO1L	29/786 ✓
6SE		5-21393	1/29/93	JAPAN	HO1L	21/302 ✓
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6SE		Improvement of structural and electrical properties in low-temperature gate oxides for poly-Si TFTs by controlling O ₂ /SiH ₄ ratios, Yuda, Tanabe and Okumura, AM-LCD 97, The Japan Society of Applied Physics, Digest of Technical Papers, 1997, International Workshop on Active-Matrix Liquid-Crystal Displays - TFT Technologies and Related Materials, September 11-12, 1997, Kogakuin University, Tokyo, Japan, pages 87-89				
6SE		Excimer Laser Crystallization of Amorphous Silicon Films, Tanabe, Sera, Nakamura, Hirata, Yuda and Okumura, reprinted from the NEC Research & Development, Vo. 35, No. 3, pp. 254-260, July 1994				
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FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS
TRANSLATION YES NO						
						
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>						
GSE		The Properties of Gases and Liquids, Robert C. Reid, John M. Prausnitz, Bruce E. Poling, Fourth Edition, Cover, Contents Page, Appendix B, page 734, and Index page.				
GSE		Transport Phenomena, Department of Chemical Engineering, University of Wisconsin, Madison, Wisconsin, Preface, pages 508-513, Table B-2, and Appendix C (page 747).				
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